

Claims

- [c1] 1. An under bump metallurgic (UBM) layer adapted for a chip, the chip comprising a bonding pad and a transmission line coupled thereto, wherein the UBM layer is formed over the bonding pad, wherein a portion of the UBM layer which is close to the transmission line is thicker than a portion of the UBM layer which is away from the transmission line.
- [c2] 2. The UBM layer of claim 1, wherein the UBM layer comprises a plurality of metal layers and at least one liner layer, the liner layer is formed among the metal layers, and the liner layer is close to an end of the transmission line which is connected to the bonding pad .
- [c3] 3. The UBM layer of claim 2, wherein the liner layer comprises a material the same as a material of at least one of the metal layers.
- [c4] 4. The UBM layer of claim 1, wherein a material of the UBM layer is selected from the group consisting of Al, Ti, W, Cr, Ni, Cu, Au, and an alloy thereof.
- [c5] 5. The UBM layer of claim 1, wherein the UBM layer comprises a plurality of metal layers, and at least one of the

metal layers at a region which is close to the transmission line is thicker than that which is away from the transmission line.

- [c6] 6. A conductive structure over a bonding pad, adapted for a chip, the chip comprising a bonding pad and a transmission line coupled thereto, the conductive structure comprising:
 - an under bump metallurgical (UBM) layer formed over the bonding pad, a portion of the UBM layer which is close to the transmission line is thicker than a portion of the UBM layer which is away from the transmission line;
 - and
 - a conductive bump, wherein a bottom of the conductive bump is connected to the UBM layer.
- [c7] 7. The conductive structure of claim 6, wherein the UBM layer comprises a plurality of metal layers and at least one liner layer, the liner layer is formed among the metal layers, and the liner layer is close to an end of the transmission line which is connected to the bonding pad.
- [c8] 8. The conductive structure of claim 7, wherein the liner layer comprises a material the same as a material of at least one of the metal layers.
- [c9] 9. The conductive structure of claim 6, wherein a mate-

rial of the UBM layer is selected from the group consisting of Al, Ti, W, Cr, Ni, Cu, Au, and an alloy thereof.

- [c10] 10. The conductive structure of claim 6, wherein the UBM layer comprises a plurality of metal layers, and at least one of the metal layers at a region which is close to the transmission line is thicker than that which is away from the transmission line.
- [c11] 11. The conductive structure of claim 6, wherein the conductive bump comprises a Sn-Pb alloy.